

## ENHANCED PROTECTION FOR INPUT BUFFERS OF LOW-VOLTAGE FLASH MEMORIES

### Abstract of the Disclosure

5           An input buffer is discussed that inhibits semiconductor breakdown of thin  
gate-oxide transistors in low-voltage integrated circuits. One aspect of the input  
buffer includes an input stage having a gate, a drain, and a source. The gate of the  
input stage is receptive to an inhibiting signal, and the drain is receptive to an input  
signal. The input stage inhibits the input signal from being presented at the source  
10 of the input stage when the inhibiting signal is at a predetermined level. The input  
buffer further includes an output stage having an inverter that includes a first  
connection and a second connection. The first connection couples to the source of  
the input stage, and the second connection presents the input signal to a low-voltage  
flash memory device.

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